

Cree® Direct Attach™ DA1000™ LEDs

CxxxDA1000-Sxxx00-2-G

Data Sheet

Cree's DA™ LEDs are the next generation of solid-state LED emitters that combine highly efficient InGaN materials with Cree's proprietary device technology and silicon-carbide substrates to deliver superior value for the general-illumination market. The DA LEDs are among the brightest in the lighting market while delivering a low forward voltage, resulting in a very bright and highly efficient solution. The bondpad-down configuration is designed for a flux eutectic die-attach process, eliminating the need for wire bonds, and enables superior performance from improved thermal management.

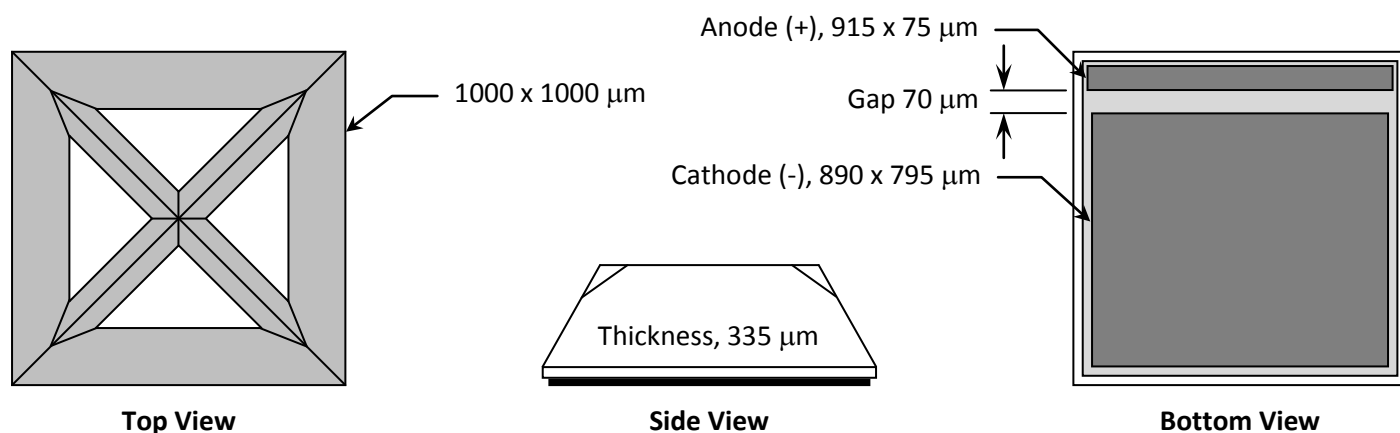
FEATURES

- Direct Attach LED Technology
- Rectangular LED RF Performance
 - 445-475 nm – 485+ mW
 - 527 nm – 200+ mW
- High Reliability - Eutectic Attach
- Low Forward Voltage (Vf) – 3.15 V Typical at 350 mA
- Maximum DC Forward Current – 1000 mA
- Junction-Down for Improved Thermal Management
- No Wire Bonds Required

APPLICATIONS

- General Illumination
 - Aircraft
 - Decorative Lighting
 - Task Lighting
 - Outdoor Illumination
- White LEDs
- Camera Flash
- Projection Displays
- Automotive

CxxxDA1000-Sxxx00-2-G Chip Diagram



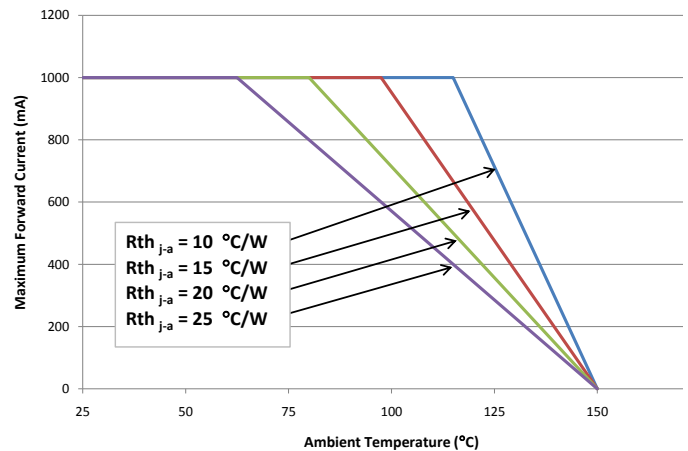
Maximum Ratings at $T_A = 25^\circ\text{C}$ <small>Notes 1,2 & 3</small>		CxxxDA1000-Sxxx00-2-G
DC Forward Current		1000 mA
Peak Forward Current (1/10 duty cycle @ 1 kHz)		1500 mA
LED Junction Temperature		150°C
Reverse Voltage		5 V
Operating Temperature Range		-40°C to +100°C
LED Chip Storage Temperature		-40°C to +120°C
Recommended Die Sheet Storage Conditions		$\leq 30^\circ\text{C}$ / $\leq 85\%$ RH

Typical Electrical/Optical Characteristics at $T_A = 25^\circ\text{C}$, $I_f = 350\text{ mA}$ <small>Note 2</small>					
Part Number	Forward Voltage (V_f , V)			Reverse Current [$I(V_r=5V)$, μA]	Full Width Half Max (λ_{DF} , nm)
	Min.	Typ.	Max.	Max.	Typ.
C450DA1000-Sxxx00-2-G	2.9	3.15	3.4	2	20
C460DA1000-Sxxx00-2-G	2.9	3.15	3.4	2	21
C470DA1000-Sxxx00-2-G	2.9	3.15	3.4	2	22
C527DA1000-Sxxx00-2-G	3.0	3.3	3.6	2	35

Mechanical Specifications		CxxxDA1000-Sxxx00-2-G	
Description	Dimension	Tolerance	
P-N Junction Area (μm)	960 x 960	± 35	
Chip Bottom Area (μm)	1000 x 1000	± 35	
Chip Top Area (μm)	630 x 630	± 45	
Chip Thickness (μm)	335	± 25	
Bond Pad Width – Anode (μm)	75	± 15	
Bond Pad Length – Anode (μm)	915	± 35	
Bond Pad Width – Cathode (μm)	795	± 35	
Bond Pad Length – Cathode (μm)	890	± 35	
Bond Pad Gap (μm)	70	± 15	
Bond Pad Thickness (μm)	3	± 0.5	

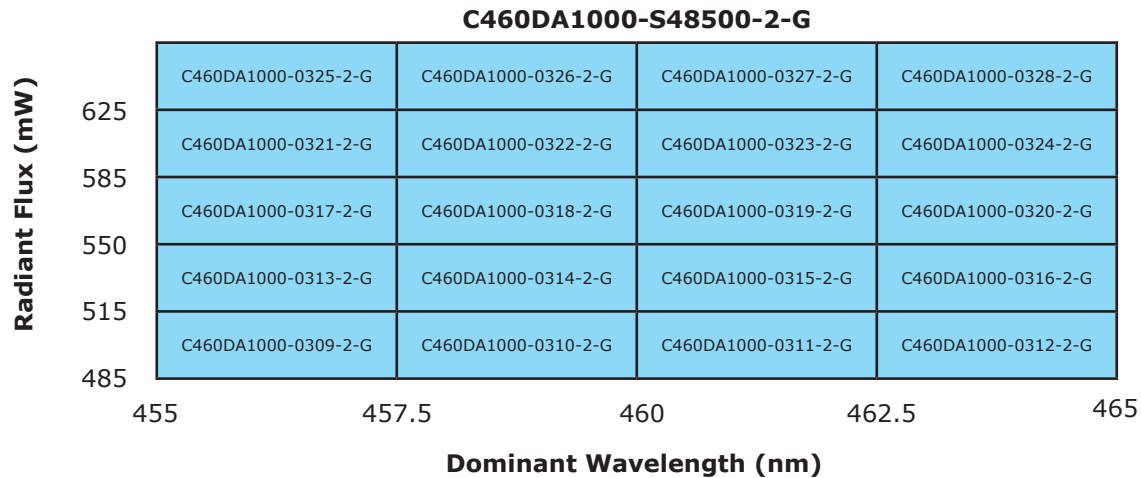
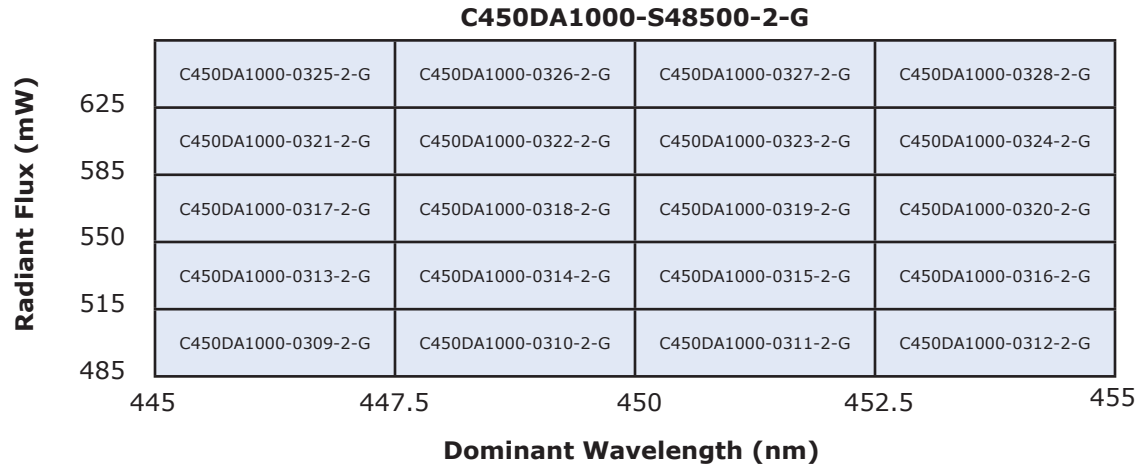
Notes:

- Maximum ratings are package-dependent. The above ratings were determined using a Cree 3.45-mm x 3.45-mm SMT package (with silicone encapsulation and flux eutectic die attach) for characterization. Ratings for other packages may differ. Junction temperature should be characterized in a specific package to determine limitations. Assembly processing temperature must not exceed 325°C (< 5 seconds).
- All products conform to the listed minimum and maximum specifications for electrical and optical characteristics when assembled and operated at 350 mA within the maximum ratings shown above. Efficiency decreases at higher currents. Typical values given are within the range of average values expected by manufacturer in large quantities and are provided for information only. All measurements were made using lamps in T-1¾ packages (with Hysol OS4000 epoxy encapsulant and flux eutectic die attach). Optical characteristics measured in an integrating sphere using Illuminance E.
- The maximum forward current is determined by the thermal resistance between the LED junction and ambient. It is crucial for the end-product to be designed in a manner that minimizes the thermal resistance from the LED junction to ambient in order to optimize product performance.



Standard Bins for CxxxDA1000-Sxxx00-2-G

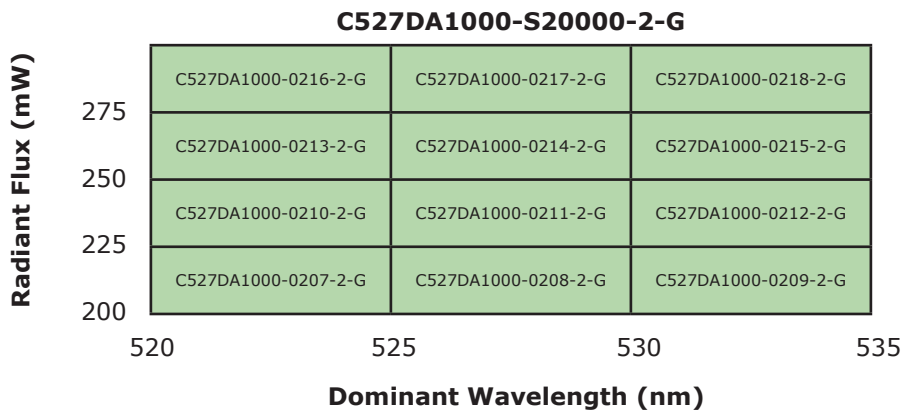
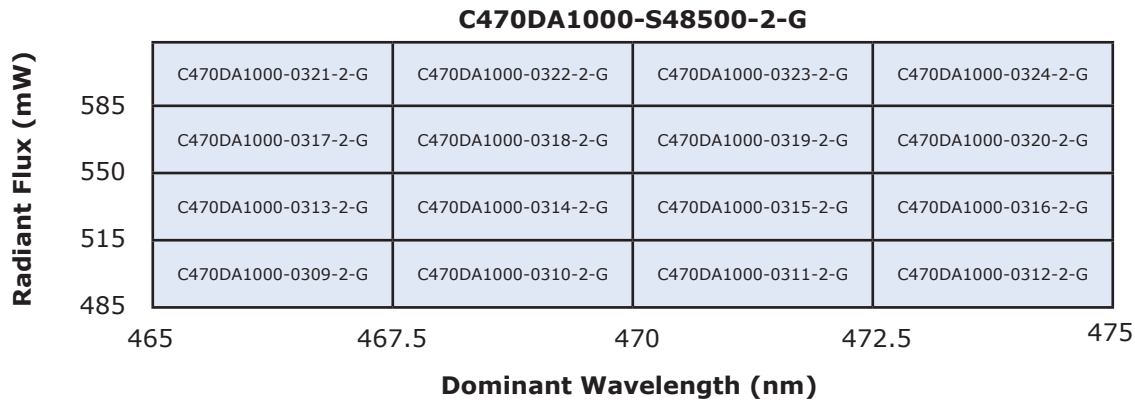
LED chips are sorted to the **radiant flux** and **dominant wavelength** bins shown. A sorted die sheet contains die from only one bin. Sorted die kit (CxxxDA1000-Sxxxxx-2-G) orders may be filled with any or all bins (CxxxDA1000-xxxx-2-G) contained in the kit. All radiant flux and dominant wavelength values shown and specified are at $I_f = 350$ mA.



Note: The radiant-flux values above are representative of the die in a T-1 $\frac{3}{4}$ encapsulated 5-mm lamp.

Standard Bins for CxxxDA1000-Sxxxx00-2-G

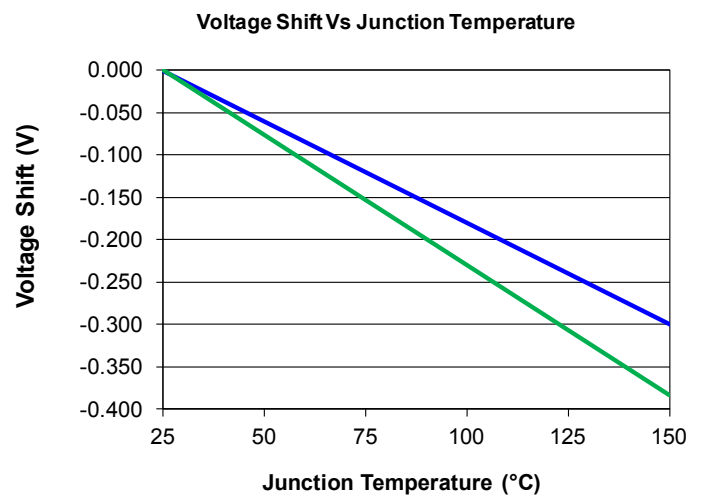
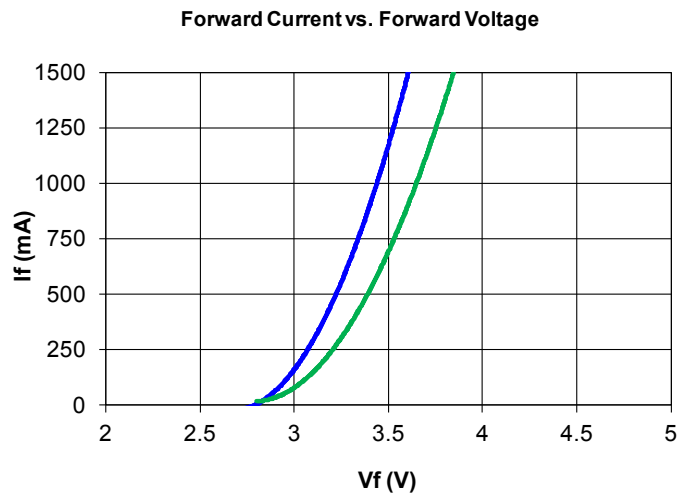
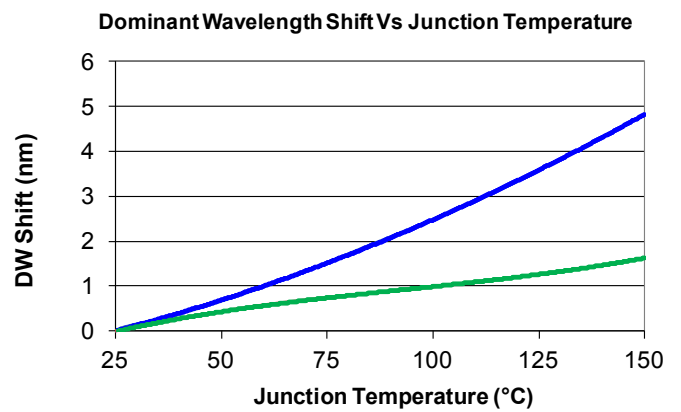
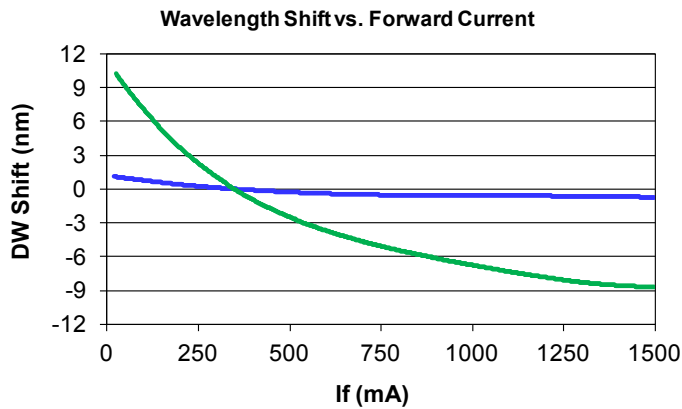
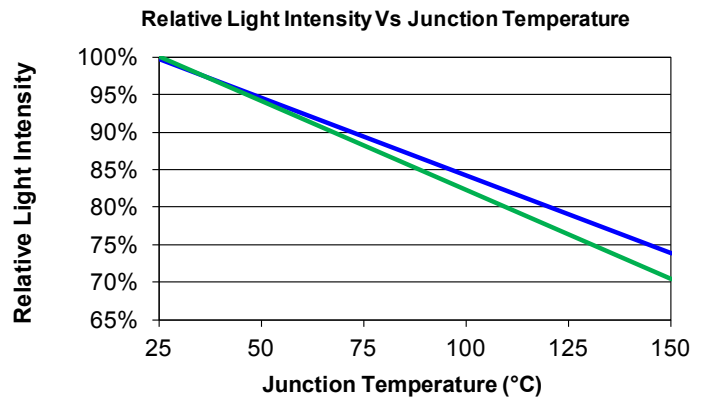
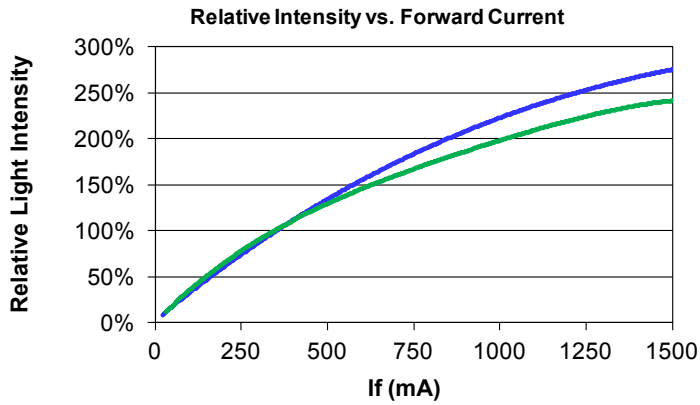
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Note: The radiant-flux values above are representative of the die in a T-1 $\frac{3}{4}$ encapsulated 5-mm lamp.

Characteristic Curves

These are representative measurements for the DA LED product. Actual curves will vary slightly for the various radiant flux and dominant wavelength bins.



Radiation Pattern

This is a representative radiation pattern for the DA LED product. Actual patterns will vary slightly for each chip.

